

**substance: NiO**

**property: transport properties in Li doped NiO**

Lithium enters NiO substitutionally, compensation being by the formation of  $\text{Ni}^{3+} - \text{Li}^+$  dipoles that are only slightly dissociated at 300 K. In addition some compensation by  $\text{V}_\text{O}$  formation is found, with profound effects on semiconductor statistics [70A].

**Figures:** effect of lithiation on  $T_\text{N}$ : Fig. 3, on resistivity: Fig. 4 (change in activation energy closely following  $T_\text{N}$ ), resistivity in the exhaustion region: Fig. 5, Seebeck coefficient: Fig. 6, and comparison with resistivity: Fig. 7. The activation energy of 0.3 eV observed is entirely due to the variation in free-hole concentration above 140 K. Below this temperature impurity conduction apparently dominates.

**Hall mobilities:** Figs. 1, 8; calculated from Seebeck coefficient: Figs. 2, 9. Sign inversion of  $R_\text{H}$  occurs at  $T_\text{N}$  as in pure NiO. Further data: [67K, 65K2, 64R]. It has been established that the activation energy for conduction falls with increasing Li content both above and below the break near  $T_\text{N}$  (Fig. 10).

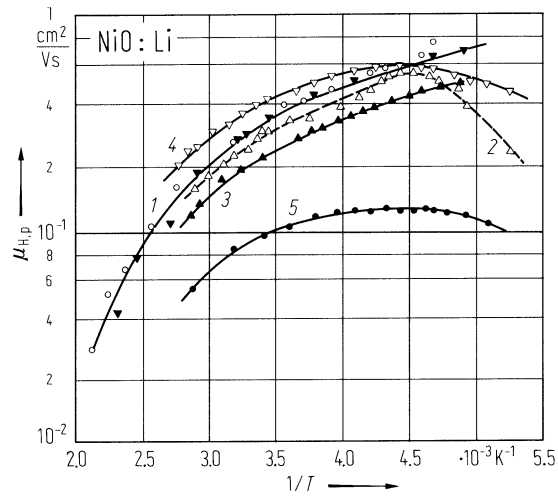
$\mu_\text{H}$	0.1...0.4 $\text{cm}^2/\text{V s}$	$T = 300 \text{ K}$	Li content: 0.005...0.088 at % Li	70B
$\mu_\text{dr}$	0.5...5.0 $\text{cm}^2/\text{V s}$			
	0.4 $\text{cm}^2/\text{V s}$	higher temperatures, exhaustion region		
$\mu_\text{H}$	$\exp(0.08[\text{eV}]/kT)$	$T = 200...400 \text{ K}$	data support large-polaron model ( $m^{**} \approx 6 m_0$ ) [70B]	70B, 67K

## References:

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- 70A Adler, D., Feinleib, J.: Phys. Rev. B2 (1970) 3112.
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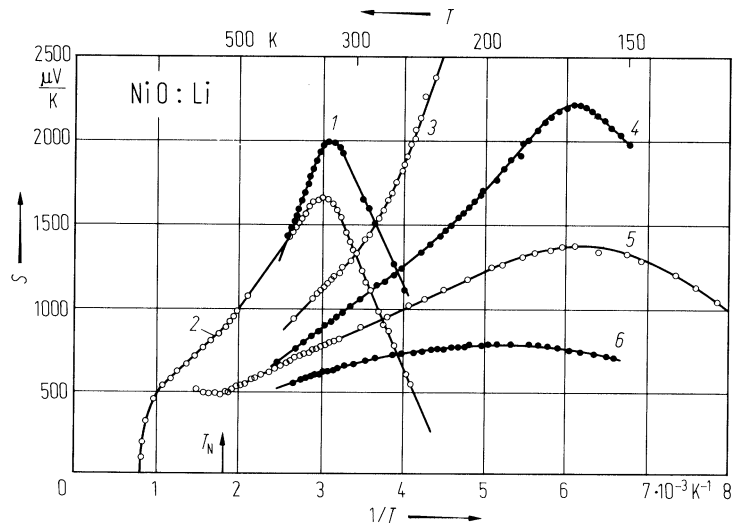
**Fig. 1.**

NiO:Li. Hall mobility for holes vs. reciprocal temperature for various single crystal samples doped with Li. at% Li: 1 (open circles: 0.032; triangles: 0.029), 2 0.144, 3 0.211, 4 0.202, 5 0.537 [67A].



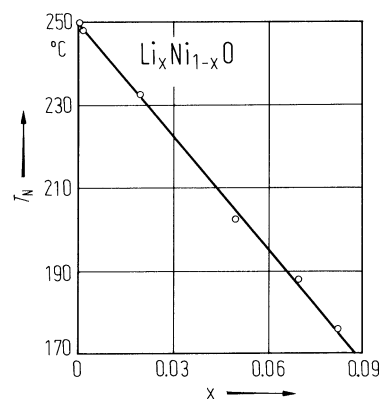
**Fig. 2.**

NiO:Li. Seebeck coefficient vs. (reciprocal) temperature for several pure and Li doped crystals. at% Li: 1 0, 2 0, 3 0.032, 4 0.202, 5 0.211, 6 0.537 [67A].



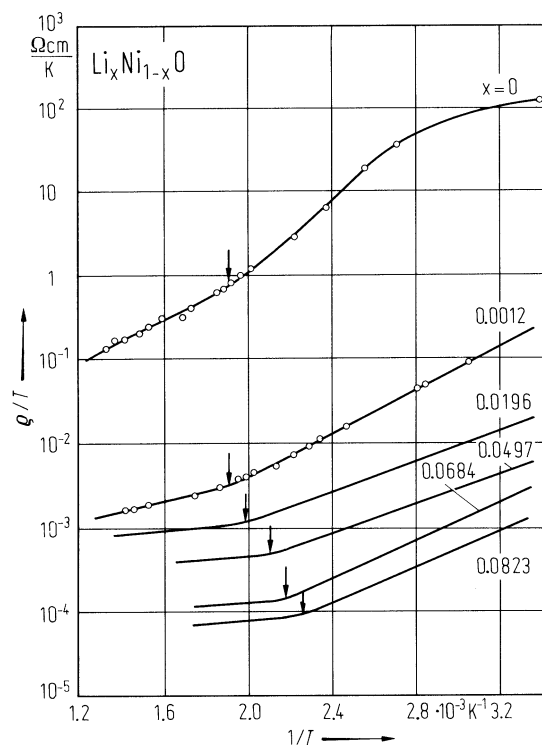
**Fig. 3.**

$\text{Li}_x\text{Ni}_{1-x}\text{O}$ . Néel temperature vs. Li concentration [73N].



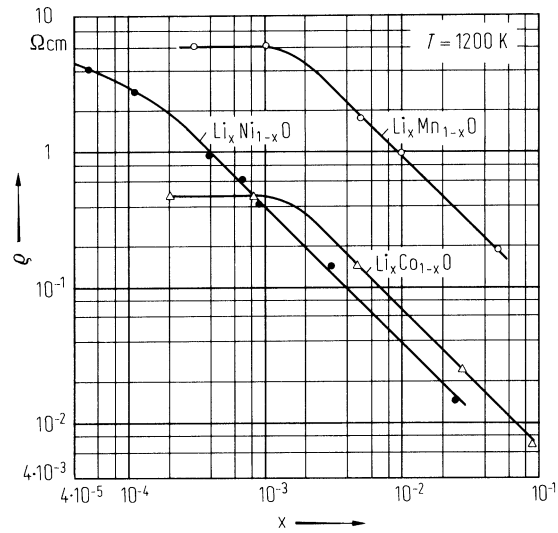
**Fig. 4.**

$\text{Li}_x\text{Ni}_{1-x}\text{O}$ . Resistivity (over  $T$ ) vs. reciprocal temperature for different doping levels. The arrows indicate  $T_N$  for each sample [73N].



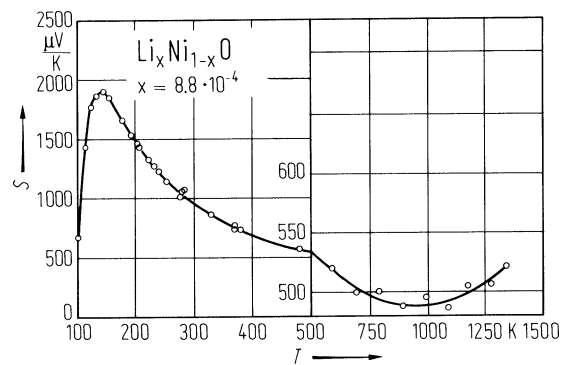
**Fig. 5.**

$\text{Li}_x\text{Ni}_{1-x}\text{O}$ . Resistivity vs. Li doping at  $T = 1200\text{ K}$  for NiO, CoO and MnO. Deviation from the linear behaviour at low doping concentration are due to the pressure of cation vacancies [70B].



**Fig. 6.**

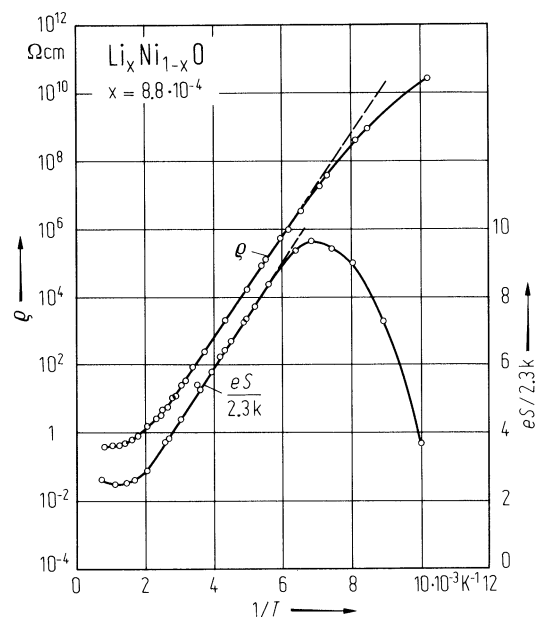
$\text{Li}_x\text{Ni}_{1-x}\text{O}$ . Seebeck coefficient vs. temperature for a sample containing  $8.8 \cdot 10^{-2}$  at% Li. Note the change in both scales at 500 K [66B].





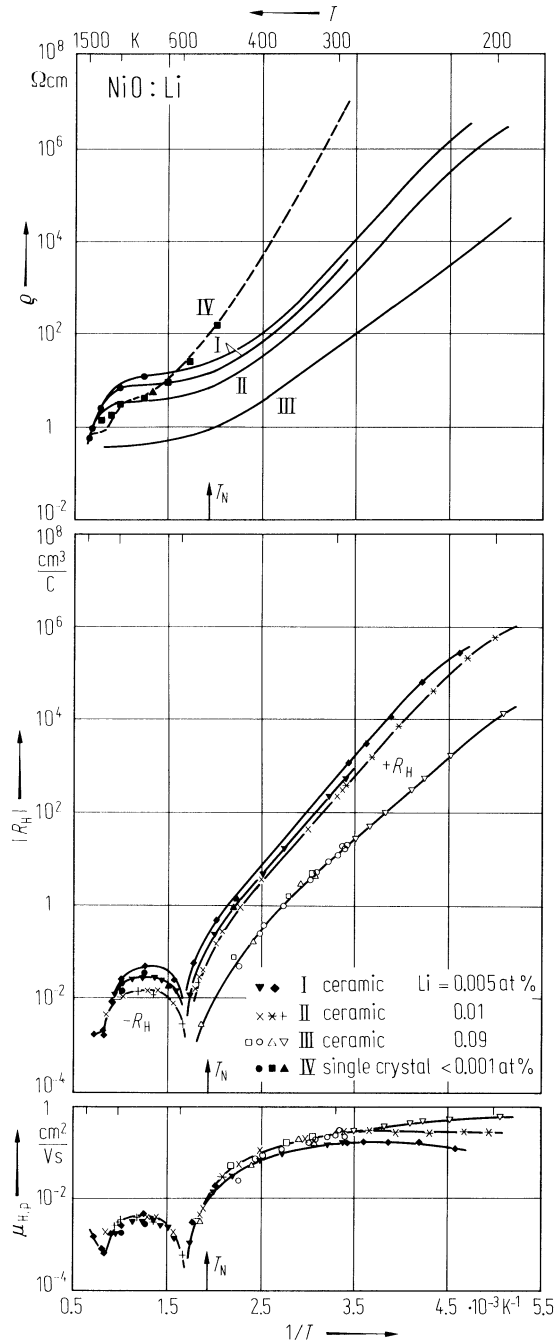
**Fig. 7.**

$\text{Li}_x\text{Ni}_{1-x}\text{O}$ . Resistivity and reduced Seebeck coefficient vs. reciprocal temperature for a sample containing  $8.8 \cdot 10^{-2}$  at% Li [66B].



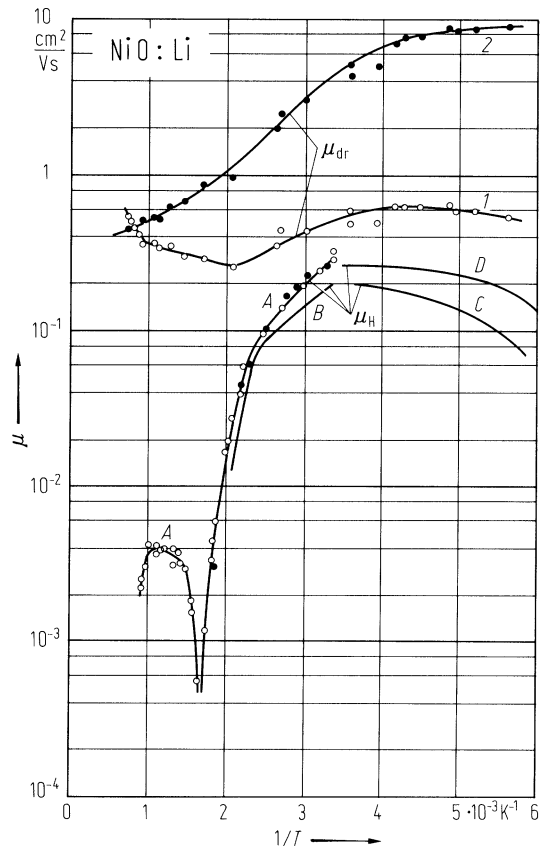
**Fig. 8.**

NiO:Li. Resistivity, Hall coefficient and Hall mobility vs. (reciprocal) temperature for p-type ceramic and non-deliberately-doped single crystal material. Values of  $\rho$  for ceramic samples have been indicated by solid lines solely. With regard to the resistivity of single crystals at high temperatures the black circles and squares represent different values for a thin disk measured when cooling the sample slowly and rapidly, respectively. The broken line results from a rapid run performed on a thick bar [67D].



**Fig. 9.**

NiO:Li. Mobility 1, 2 and Hall mobility A...D for holes vs. reciprocal temperature. 1, 2 0.088 at% Li doped, calculated  $\sigma$  and  $S$  using different approximations. A Li doped crystals with 0.088...0.005 at%, B single crystal undoped and C, D single crystals 0.2 at% Li doped [66B].



**Fig. 10.**

$\text{Li}_x\text{Ni}_{1-x}\text{O}$ . Activation energy vs. Li content for two specimens. Full circles:  $E_{A1}$  for  $T > T^*$ , open circles:  $E_{A2}$  for  $T < T^*$  where  $T^*$  is the temperature at which a break occurs in the  $\log \sigma$  vs.  $1/T$  plot and  $E_{A1}$  and  $E_{A2}$  are the activation energies  $T >$  and  $< T^*$  [65K1].

